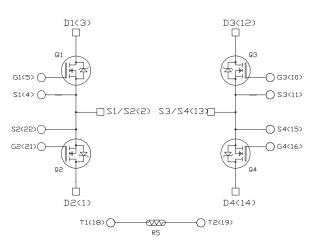
MSCSM120DDUM16TBL3NG

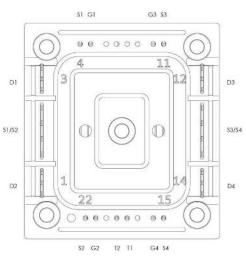
Double Dual Common Source SiC MOSFET Power Module

Product Overview

The MSCSM120DDUM16TBL3NG device is a double dual common source 1200V, 150A silicon carbide (SiC) MOSFET power module.







Note: All ratings at $T_J = 25$ °C, unless otherwise specified.

⚠ CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM120DDUM16TBL3NG device:

- · SiC Power MOSFET
 - High speed switching
 - Low R_{DS(on)}
- · Ultra-low weight and profile
- Kelvin source for easy drive
- Si₃N₄ substrate with thick copper for improved thermal performance
- · Internal thermistor for temperature monitoring
- Extended temperature range

Benefits

The following are the benefits of MSCSM120DDUM16TBL3NG device:

- · High efficiency converter
- · Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very integrated power conversion system
- Low profile
- RoHS compliant

Application

The following are the applications of MSCSM120DDUM16TBL3NG device:

- · High reliability power systems
- · AC switches

DS00004653A-page 2 **Data Sheet**

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120DDUM16TBL3NG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V _{DSS}	Drain-Source voltage	Drain-Source voltage		V
I _D	Continuous drain current T _H = 25 °C		150	Α
		T _H = 80 °C	120	
I _{DM}	Pulsed drain current	Pulsed drain current		
V _{GS}	Gate-Source voltage	Gate-Source voltage		V
R _{DS(on)}	Drain-Source ON resistance		16	mΩ
P _D	Power dissipation	T _H = 25 °C	560	W

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristics	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V; V _{DS} = 1200V		_	20	200	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	_	12.5	16	mΩ
	resistance	$I_D = 80A$ $T_J = 175 °C$		_	20	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$; $I_D = 6 \text{ mA}$		1.8	2.8	_	V
I _{GSS}	Gate–Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$		_	_	200	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristics	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	6040	_	pF
C _{oss}	Output capacitance	V _{DS} = 1000V		_	540	_	
C _{rss}	Reverse transfer capacitance	f = 1 MHz		_	50	_	
Qg	Total gate charge	$V_{GS} = -5V/20V$		_	464	_	nC
Q _{gs}	Gate-Source charge	V _{Bus} = 800V		_	82	_	
Q _{gd}	Gate-Drain charge	I _D = 80A	I _D = 80A			_	
T _{d(on)}	Turn-on delay time	$V_{GS} = -5V/20V$	_	30	_	ns	
T _r	Rise time	V _{Bus} = 600V		_	30	_	
T _{d(off)}	Turn-off delay time	I _D = 100A		_	50	_	
T _f	Fall time	$R_{G(on)} = 4\Omega$ $R_{G(off)} = 2.4\Omega$				_	
E _{on}	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C	_	2.4	_	mJ
E _{off}	Turn-off energy	$V_{Bus} = 600V$ $I_{D} = 100A$ $R_{G(on)} = 4\Omega$ $R_{G(off)} = 2.4\Omega$		_	1.3	_	
R _{Gint}	Internal gate resistance				1.94	_	Ω
R _{thJH}	Junction-to-heatsink the	ermal resistance	$\lambda = 3.4 \text{ W/mK}$	_	0.268	_	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 80A$	_	4	_	V
		$V_{GS} = -5V; I_{SD} = 80A$	_	4.2	_	
t _{rr}	Reverse recovery time	$I_{SD} = 80A; V_{GS} = -5V$	_	90	_	ns
Q _{rr}	Reverse recovery charge	$V_R = 800V$; $di_F/dt = 2000 A/\mu s$	_	1100	_	nC
I _{rr}	Reverse recovery current		_	27	_	Α

1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120DDUM16TBL3NG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristics			Min.	Тур.	Max.	Unit
V _{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			2500	_	_	V
TJ	Operating junction temperature range			- 55	_	175	°C
T _{JOP}	Recommended junction temperature under switching conditions			- 55	_	T _{Jmax} –25	
T _{STG}	Storage case temperature			- 55	_	125	
T _C	Operating case temperature			- 55	_	125	
Torque	Mounting torque To heatsink M3			0.7	_	0.9	N.m
Wt	Package weight			_	32.5	_	g

The following table lists the temperature sensor NTC of the MSCSM120DDUM16TBL3NG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristics		Min.	Тур.	Max.	Unit
R ₂₅	Resistance at 25 °C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_	_	5	_	%	
B _{25/85}	T ₂₅ = 298.15K		_	3952	_	K
ΔΒ/Β	_	T _C = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 R_T: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120DDUM16TBL3NG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance

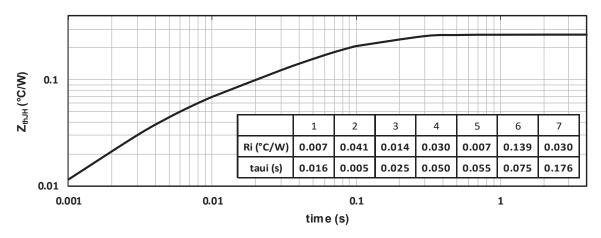


Figure 1-2. Output Characteristics, $T_J = 25$ °C

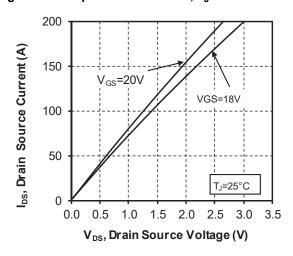


Figure 1-3. Output Characteristics, T_J = 175 °C

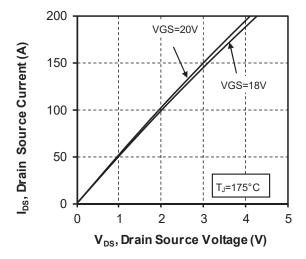


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

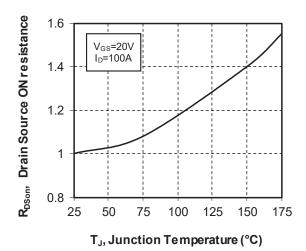


Figure 1-5. Transfer Characteristics

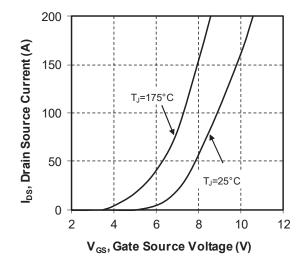


Figure 1-6. Switching Energy vs. Rg

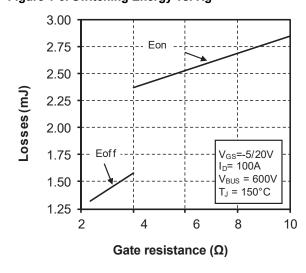


Figure 1-7. Switching Energy vs. Current

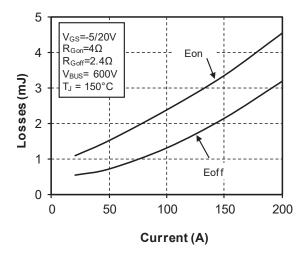


Figure 1-8. Capacitance vs. Drain Source Voltage

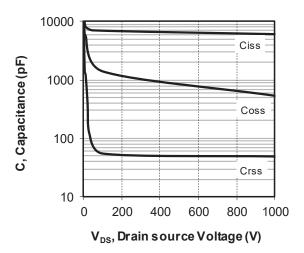


Figure 1-9. Gate Charge vs. Gate Source Voltage

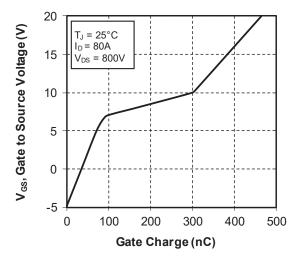


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

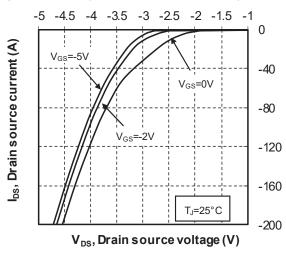


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

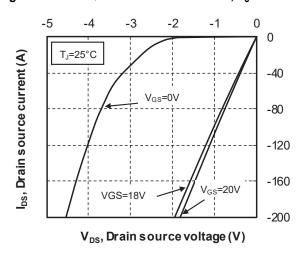
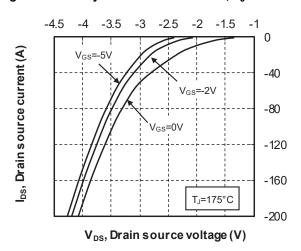


Figure 1-12. Body Diode Characteristics, T_J = 175 °C Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C



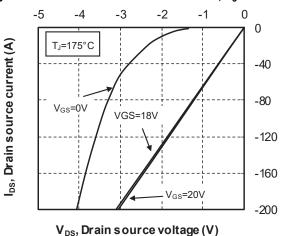
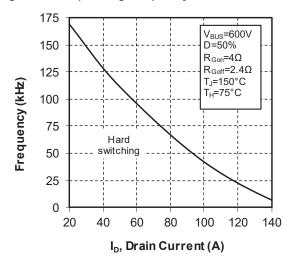


Figure 1-14. Operating Frequency vs Drain Current



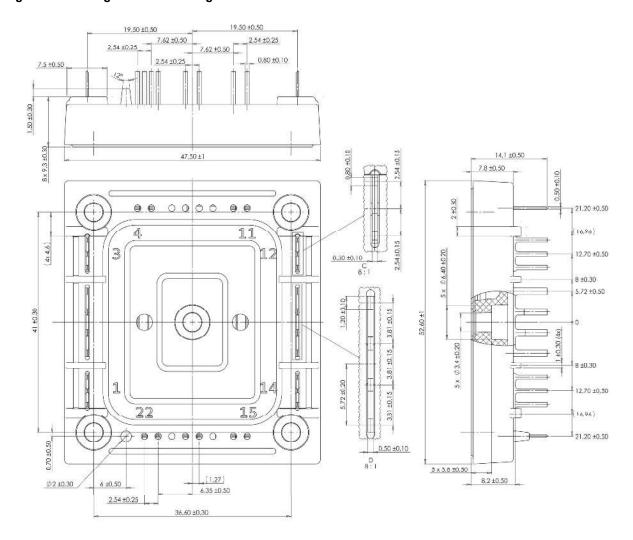
2. Package Specifications

The following section shows the package specification of the MSCSM120DDUM16TBL3NG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120DDUM16TBL3NG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN4306 — Mounting Instructions for Baseless Power Module for more information.

MSCSM120DDUM16TBL3NG

Revision History

3. Revision History

Revision	Date	Description
Α	06/2022	Initial Revision

Microchip Information

The Microchip Website

Microchip provides online support via our website at www.microchip.com/. This website is used to make files and information easily available to customers. Some of the content available includes:

- Product Support Data sheets and errata, application notes and sample programs, design resources, user's guides and hardware support documents, latest software releases and archived software
- General Technical Support Frequently Asked Questions (FAQs), technical support requests, online discussion groups, Microchip design partner program member listing
- Business of Microchip Product selector and ordering guides, latest Microchip press releases, listing of seminars and events, listings of Microchip sales offices, distributors and factory representatives

Product Change Notification Service

Microchip's product change notification service helps keep customers current on Microchip products. Subscribers will receive email notification whenever there are changes, updates, revisions or errata related to a specified product family or development tool of interest.

To register, go to www.microchip.com/pcn and follow the registration instructions.

Customer Support

Users of Microchip products can receive assistance through several channels:

- Distributor or Representative
- Local Sales Office
- Embedded Solutions Engineer (ESE)
- **Technical Support**

Customers should contact their distributor, representative or ESE for support. Local sales offices are also available to help customers. A listing of sales offices and locations is included in this document.

Technical support is available through the website at: www.microchip.com/support

Microchip Devices Code Protection Feature

Note the following details of the code protection feature on Microchip products:

- Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner, within operating specifications, and under normal conditions.
- Microchip values and aggressively protects its intellectual property rights. Attempts to breach the code protection features of Microchip product is strictly prohibited and may violate the Digital Millennium Copyright
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code protection does not mean that we are guaranteeing the product is "unbreakable". Code protection is constantly evolving. Microchip is committed to continuously improving the code protection features of our products.

Legal Notice

This publication and the information herein may be used only with Microchip products, including to design, test, and integrate Microchip products with your application. Use of this information in any other manner violates these terms. Information regarding device applications is provided only for your convenience and may be superseded

DS00004653A-page 12 **Data Sheet** © 2022 Microchip Technology Inc.

by updates. It is your responsibility to ensure that your application meets with your specifications. Contact your local Microchip sales office for additional support or, obtain additional support at www.microchip.com/en-us/support/design-help/client-support-services.

THIS INFORMATION IS PROVIDED BY MICROCHIP "AS IS". MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION INCLUDING BUT NOT LIMITED TO ANY IMPLIED WARRANTIES OF NON-INFRINGEMENT, MERCHANTABILITY, AND FITNESS FOR A PARTICULAR PURPOSE, OR WARRANTIES RELATED TO ITS CONDITION, QUALITY, OR PERFORMANCE.

IN NO EVENT WILL MICROCHIP BE LIABLE FOR ANY INDIRECT, SPECIAL, PUNITIVE, INCIDENTAL, OR CONSEQUENTIAL LOSS, DAMAGE, COST, OR EXPENSE OF ANY KIND WHATSOEVER RELATED TO THE INFORMATION OR ITS USE, HOWEVER CAUSED, EVEN IF MICROCHIP HAS BEEN ADVISED OF THE POSSIBILITY OR THE DAMAGES ARE FORESEEABLE. TO THE FULLEST EXTENT ALLOWED BY LAW, MICROCHIP'S TOTAL LIABILITY ON ALL CLAIMS IN ANY WAY RELATED TO THE INFORMATION OR ITS USE WILL NOT EXCEED THE AMOUNT OF FEES, IF ANY, THAT YOU HAVE PAID DIRECTLY TO MICROCHIP FOR THE INFORMATION.

Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

Trademarks

The Microchip name and logo, the Microchip logo, Adaptec, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, CryptoMemory, CryptoRF, dsPIC, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AgileSwitch, APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, Flashtec, Hyper Speed Control, HyperLight Load, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet- Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, TrueTime, and ZL are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, Anyln, AnyOut, Augmented Switching, BlueSky, BodyCom, Clockstudio, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, Espresso T1S, EtherGREEN, GridTime, IdealBridge, In-Circuit Serial Programming, ICSP, INICnet, Intelligent Paralleling, IntelliMOS, Inter-Chip Connectivity, JitterBlocker, Knob-on-Display, KoD, maxCrypto, maxView, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, RTAX, RTG4, SAM-ICE, Serial Quad I/O, simpleMAP, SimpliPHY, SmartBuffer, SmartHLS, SMART-I.S., storClad, SQI, SuperSwitcher, SuperSwitcher II, Switchtec, SynchroPHY, Total Endurance, Trusted Time, TSHARC, USBCheck, VariSense, VectorBlox, VeriPHY, ViewSpan, WiperLock, XpressConnect, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, and Symmcom are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2022, Microchip Technology Incorporated and its subsidiaries. All Rights Reserved.

ISBN: 978-1-6683-0818-9

© 2022 Microchip Technology Inc. Data Sheet DS00004653A-page 13 and its subsidiaries

MSCSM120DDUM16TBL3NG

Quality Management System

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.

DS00004653A-page 14 **Data Sheet**



Worldwide Sales and Service

AMERICAS	ASIA/PACIFIC	ASIA/PACIFIC	EUROPE
Corporate Office	Australia - Sydney	India - Bangalore	Austria - Wels
2355 West Chandler Blvd.	Tel: 61-2-9868-6733	Tel: 91-80-3090-4444	Tel: 43-7242-2244-39
Chandler, AZ 85224-6199	China - Beijing	India - New Delhi	Fax: 43-7242-2244-393
Tel: 480-792-7200	Tel: 86-10-8569-7000	Tel: 91-11-4160-8631	Denmark - Copenhagen
Fax: 480-792-7277	China - Chengdu	India - Pune	Tel: 45-4485-5910
Technical Support:	Tel: 86-28-8665-5511	Tel: 91-20-4121-0141	Fax: 45-4485-2829
www.microchip.com/support	China - Chongqing	Japan - Osaka	Finland - Espoo
Web Address:	Tel: 86-23-8980-9588	Tel: 81-6-6152-7160	Tel: 358-9-4520-820
www.microchip.com	China - Dongguan	Japan - Tokyo	France - Paris
Atlanta	Tel: 86-769-8702-9880	Tel: 81-3-6880- 3770	Tel: 33-1-69-53-63-20
Duluth, GA	China - Guangzhou	Korea - Daegu	Fax: 33-1-69-30-90-79
Tel: 678-957-9614	Tel: 86-20-8755-8029	Tel: 82-53-744-4301	Germany - Garching
Fax: 678-957-1455	China - Hangzhou	Korea - Seoul	Tel: 49-8931-9700
Austin, TX	Tel: 86-571-8792-8115	Tel: 82-2-554-7200	Germany - Haan
Tel: 512-257-3370	China - Hong Kong SAR	Malaysia - Kuala Lumpur	Tel: 49-2129-3766400
Boston	Tel: 852-2943-5100	Tel: 60-3-7651-7906	Germany - Heilbronn
Westborough, MA	China - Nanjing	Malaysia - Penang	Tel: 49-7131-72400
Tel: 774-760-0087	Tel: 86-25-8473-2460	Tel: 60-4-227-8870	Germany - Karlsruhe
Fax: 774-760-0088	China - Qingdao	Philippines - Manila	Tel: 49-721-625370
Chicago	Tel: 86-532-8502-7355	Tel: 63-2-634-9065	Germany - Munich
Itasca, IL	China - Shanghai	Singapore	Tel: 49-89-627-144-0
Tel: 630-285-0071	Tel: 86-21-3326-8000	Tel: 65-6334-8870	Fax: 49-89-627-144-44
Fax: 630-285-0075	China - Shenyang	Taiwan - Hsin Chu	Germany - Rosenheim
Dallas	Tel: 86-24-2334-2829	Tel: 886-3-577-8366	Tel: 49-8031-354-560
Addison, TX	China - Shenzhen	Taiwan - Kaohsiung	Israel - Ra'anana
Tel: 972-818-7423	Tel: 86-755-8864-2200	Tel: 886-7-213-7830	Tel: 972-9-744-7705
Fax: 972-818-2924	China - Suzhou	Taiwan - Taipei	Italy - Milan
Detroit	Tel: 86-186-6233-1526	Tel: 886-2-2508-8600	Tel: 39-0331-742611
Novi, MI	China - Wuhan	Thailand - Bangkok	Fax: 39-0331-466781
Tel: 248-848-4000	Tel: 86-27-5980-5300	Tel: 66-2-694-1351	Italy - Padova
Houston, TX	China - Xian	Vietnam - Ho Chi Minh	Tel: 39-049-7625286
Tel: 281-894-5983	Tel: 86-29-8833-7252	Tel: 84-28-5448-2100	Netherlands - Drunen
Indianapolis	China - Xiamen		Tel: 31-416-690399
Noblesville, IN	Tel: 86-592-2388138		Fax: 31-416-690340
Tel: 317-773-8323	China - Zhuhai		Norway - Trondheim
Fax: 317-773-5453	Tel: 86-756-3210040		Tel: 47-72884388
Tel: 317-536-2380			Poland - Warsaw
Los Angeles			Tel: 48-22-3325737
Mission Viejo, CA			Romania - Bucharest
Tel: 949-462-9523			Tel: 40-21-407-87-50
Fax: 949-462-9608			Spain - Madrid
Tel: 951-273-7800			Tel: 34-91-708-08-90
Raleigh, NC			Fax: 34-91-708-08-91
Tel: 919-844-7510			Sweden - Gothenberg
New York, NY Tel: 631-435-6000			Tel: 46-31-704-60-40 Sweden - Stockholm
San Jose, CA			Tel: 46-8-5090-4654
Tel: 408-735-9110			UK - Wokingham
Tel: 408-436-4270			Tel: 44-118-921-5800
Canada - Toronto Tel: 905-695-1980			Fax: 44-118-921-5820
Fax: 905-695-2078			
I AA. 300-030-2070			